

IN THE CLAIMS:

A complete listing of all the claims is now presented.

Claims 1 - 12. (Cancelled).

Claim 13. (Previously Presented).

A semiconductor wafer, comprising
a substrate wafer made of monocrystalline silicon and an
epitaxial layer deposited thereon;
said substrate wafer having a resistivity of from 0.1 to
50 Ωcm , an oxygen concentration of less than $7.5 \times 10^{17} \text{ atcm}^{-3}$ and a
nitrogen concentration of from 1×10^{13} to $5 \times 10^{15} \text{ atcm}^{-3}$; and
the epitaxial layer has a thickness of from 0.2 to 1.0 μm
and has a surface on which fewer than 30 LLS defects with a size
of more than 0.085 μm can be detected.

Claim 14. (Previously Presented).

The semiconductor wafer as claimed in claim 13,
wherein the oxygen concentration of the substrate wafer is
less than $6.5 \times 10^{17} \text{ atcm}^{-3}$.

Claim 15. (Previously Presented) .

The semiconductor wafer as claimed in claim 13,
wherein the nitrogen concentration of the substrate wafer

lies in a range of from 1×10^{14} to 5×10^{14} atcm⁻³.

Claim 16 to 24 (Cancelled).

Claim 25. (New).

A semiconductor wafer consisting of
a substrate wafer made of monocrystalline silicon and an
epitaxial layer deposited thereon;
said substrate wafer having a resistivity of from 0.1 to 50
 Ω cm, an oxygen concentration of less than 7.5×10^{17} atcm⁻³ and a
nitrogen concentration of from 1×10^{13} to 5×10^{15} atcm⁻³; and
the epitaxial layer has a thickness of from 0.2 to 1.0 μ m
and has a surface on which fewer than 30 LLS defects with a size
of more than 0.085 μ m can be detected.

Claim 26. (New).

The semiconductor wafer as claimed in claim 25,
wherein the oxygen concentration of the substrate wafer is
less than 6.5×10^{17} atcm⁻³.

Claim 27. (New).

The semiconductor wafer as claimed in claim 25,
wherein the nitrogen concentration of the substrate wafer
lies in a range of from 1×10^{14} to 5×10^{14} atcm⁻³.